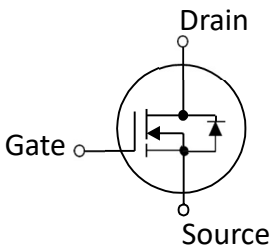
40V, 195A (1) N-Channel MOSFET

- Proprietary Trench Gate Device Design and Processes
- High Reliability Capability
- Sampled CP Probing and Inking

SYMBOL



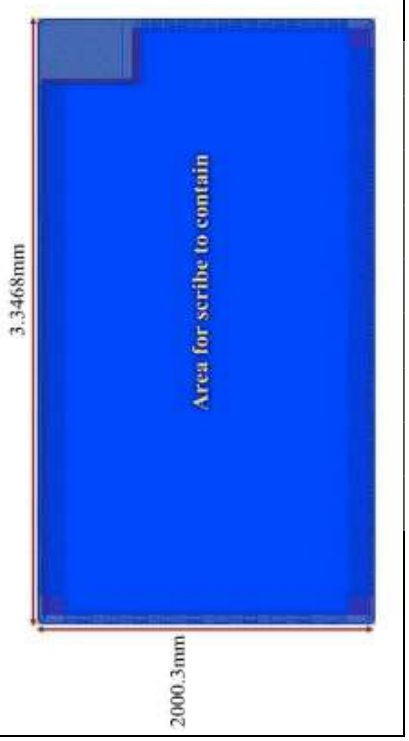
Electrical Characteristics in C/P Test (T_J at 25 ℃)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	40	—	—	V	V_{GS} =0V, I_D =250μA
$R_{DS(ON)}$	Static Drain-Source On-Resistance	—	1.1	1.3	mΩ	V_{GS} =10V, I_D =1A(2)
$V_{GS\ (th)}$	Gate Threshold Voltage	2	—	5	V	V_{DS} =V_{GS}, I_D =250μA
I_{DSS}	Drain-to-Source Leakage Current	—	—	1	μA	V_{DS} =32V, V_{GS} =0V
I_{GSS}	Gate-to-Source Leakage Current	-100	—	100	nA	V_{DS} =0V, V_{GS} =±20V
T_J, T_{STG}	Operating and Storage Temperature	-55℃ to 150℃ Max.				

Mechanical Data

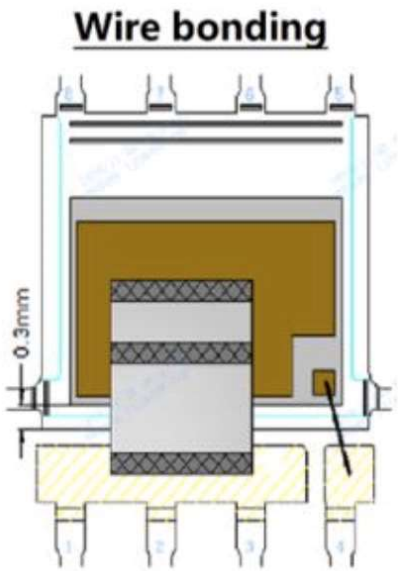
Chip Size	3345 μm X 2000 μm
Gate Pad Size	301 μm X 504 μm
Source Pad Size	3264 μm X 1917 μm
Scribe Line Width	60 μm
Wafer Thickness	150 μm
Wafer Diameter	200 mm
Gross Die	4037 EA
Source Metallization	Al-Cu (4μm typical)
Drain Metallization	Ti-Ni-Ag
Passivation	N/A
Recommended Storage Environment	Store in original container, in dry nitrogen, 6 months at ambient temperature of 23°C ± 3°C

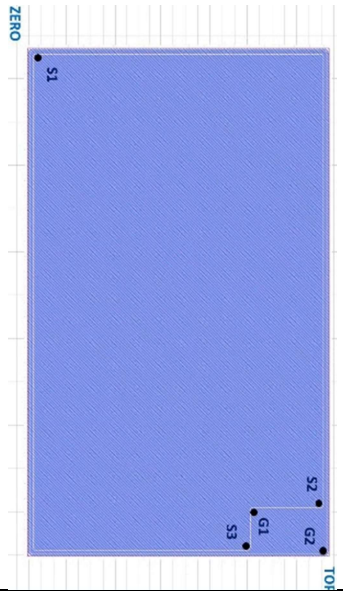
Die Drawing



(1) This characteristic assumes the die is assembled in DFN5*6 package. Actual performance may degrade when assembled.

(2) Pulse Width tp = < 1 mS, Duty Cycle < 2%.

Specific Assembly Information Bill of Material (BOM)		Die Drawing
Package Type	DFN5*6	
Die Attach Method	Soft solder	
Soft Solder Composition	Pb,Sn,Ag	
Gate Wire Bonding	Cu, 2 mil x1	
Source Wire Bonding	60mil*4mil Al Ribbon (double stitch)	
Molding Compound Manufacturer	G700HF	
Solder Plating Composition	Pure Tin	

Position			Bonding Diagram Top View
	X (um)	Y (um)	
ZERO	0	0	
TOP	3346.8	2000.3	
S1	41.6	41.6	
S2	3023.13	1958.7	
S3	3305.2	1473.55	
G1	3029.13	1479.75	
G2	3330.2	1983.7	

Electrical Characteristics in F/P Test (T_J at 25 ℃)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
I_{DSS}	Drain-to-Source Leakage Current	—	—	1	μA	V_{DS} =32V, V_{GS} =0V
I_{GSSF}	Gate-to-Source Leakage Current	—	—	100	nA	V_{DS} =0V, V_{GS} =+20V
I_{GSSR}	Gate-to-Source Leakage Current	-100	—	—	nA	V_{DS} =0V, V_{GS} =-20V
BV_{DSS}	Drain-Source Breakdown Voltage	40	—	—	V	V_{GS} =0V, I_D =250μA
BV_{DSS}	Drain-Source Breakdown Voltage	40	—	—	V	V_{GS} =0V, I_D =1mA
$R_{DS(ON)}$	Static Drain-Source On-Resistance	—	—	2.6	mΩ	V_{GS} =10V, I_D =20A
$V_{GS\ (th)}$	Gate Threshold Voltage	2	—	5	V	V_{DS} =V_{GS}, I_D =250μA
V_{SD}	Drain-Source Diode Forward Voltage			1.1	V	V_{GS} = 0V, I_{SD} = 20A
EAS test	IAS				A	VDD=40V,Vgs=10V, RG=25ohm,L=0.5mH
T_J, T_{STG}	Operating and Storage Temperature	-55℃ to 150℃ Max.				

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